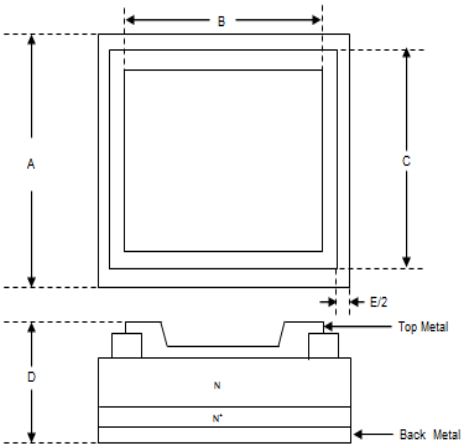
TSB130T045S(A)S-310A

20A/45V(1), low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	3302μm	130 mil
	Top Metal Pad Size (B)	3223μm	127mil
	Chip Size (C)	3251μm	128mil
	Wafer Thickness (D)	310 μm	11.4 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	Al/Ag	
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23℃±3℃)	

Electrical Characteristics (T_J=25℃, unless otherwise specified)(2)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	48	53	-	V	I_R =100μA
V_F	Instantaneous Forward Voltage	-	0.47	0.50	V	I_F =20A(3)
I_R	Reverse Leakage Current	-	13	40	μA	V_R =45V
T_J, T_{STG}	Operating and Storage Temperature	-40℃ to 150℃ Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in R-6 packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) Pulse Width tp = < 300μS, Duty Cycle <2%;